



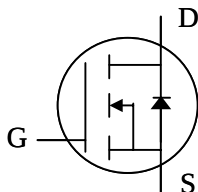
N-channel Enhancement-mode Power MOSFET

Simple Drive Requirement

Low Gate Charge

Fast Switching Performance

RoHS-compliant, halogen-free



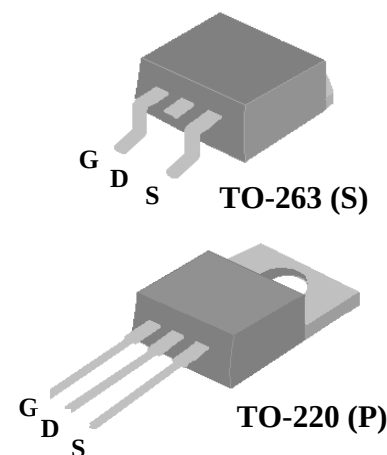
BV_{DS}	30V
$R_{DS(ON)}$	25m Ω
I_D	28A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP40T03GS-HF-3 is in the TO-263 package, which is widely used for commercial and industrial surface-mount applications, and is well suited for low voltage applications such as DC/DC converters.

The AP40T03GP-HF-3 is in the TO-220 through-hole package which is used where a low PCB footprint or an attached heatsink is required.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 25	V
I_D at $T_C=25^\circ\text{C}$	Continuous Drain Current	28	A
I_D at $T_C=100^\circ\text{C}$	Continuous Drain Current	24	A
I_{DM}	Pulsed Drain Current ¹	95	A
P_D at $T_C=25^\circ\text{C}$	Total Power Dissipation	31.25	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	4	$^\circ\text{C/W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ\text{C/W}$

Ordering Information

AP40T03GS-HF-3TR RoHS-compliant, halogen-free TO-263, shipped on tape and reel (800 pcs/reel)

AP40T03GP-HF-3TB RoHS-compliant, halogen-free TO-220, shipped in tubes



Electrical Specifications at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D=1mA$	-	0.032	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=18A$	-	-	25	$m\Omega$
		$V_{GS}=4.5V, I_D=14A$	-	-	45	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=18A$	-	15	-	S
I_{DSS}	Drain-Source Leakage Current ($T_j=25^\circ\text{C}$)	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_j=150^\circ\text{C}$)	$V_{DS}=24V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 25V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=18A$	-	8.8	-	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=20V$	-	2.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	5.8	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=15V$	-	6	-	ns
t_r	Rise Time	$I_D=18A$	-	62	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	16	-	ns
t_f	Fall Time	$R_D=0.83\Omega$	-	4.4	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	655	-	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	145	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	95	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current (Body Diode)	$V_D=V_G=0V, V_S=1.3V$	-	-	28	A
I_{SM}	Pulsed Source Current (Body Diode) ¹		-	-	95	A
V_{SD}	Forward On Voltage ²	$T_j=25^\circ\text{C}, I_S=28A, V_{GS}=0V$	-	-	1.3	V

Notes:

1. Pulse width limited by safe operating area.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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Typical Electrical Characteristics

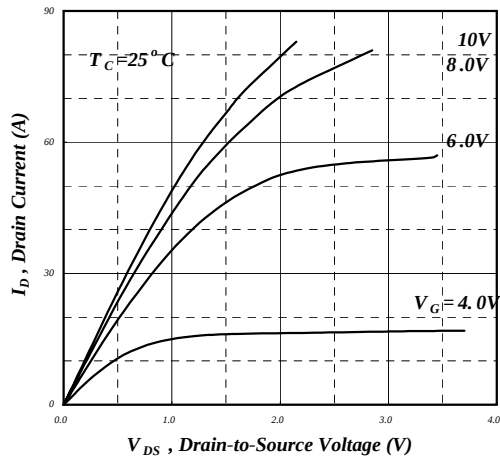


Fig 1. Typical Output Characteristics

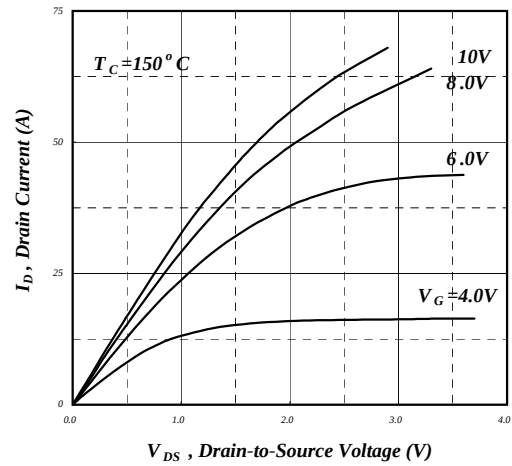


Fig 2. Typical Output Characteristics

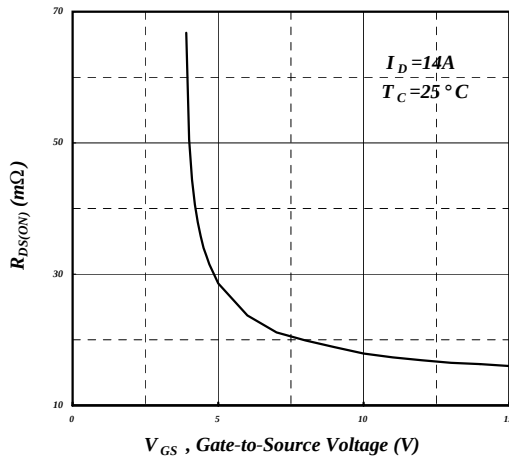


Fig 3. On-Resistance vs. Gate Voltage

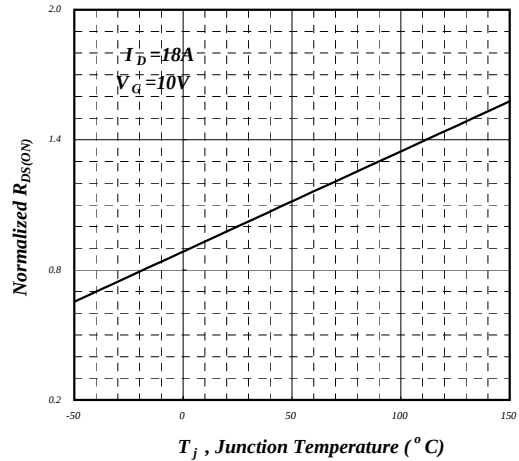


Fig 4. Normalized On-Resistance
vs. Junction Temperature

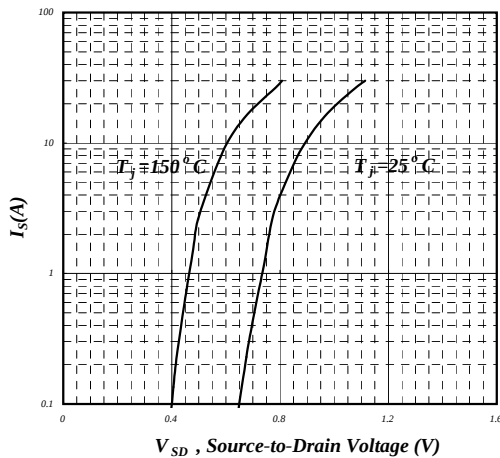


Fig 5. Forward Characteristic of
Reverse Diode

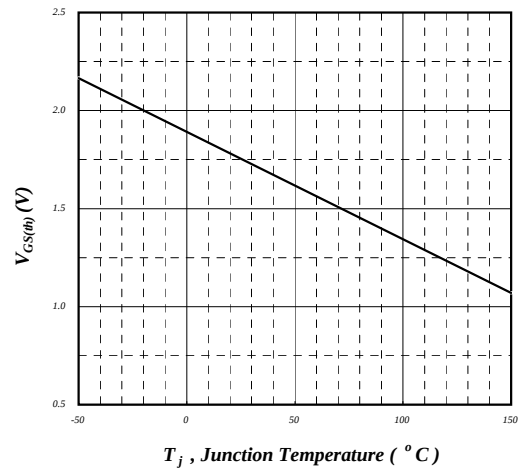


Fig 6. Gate Threshold Voltage vs.
Junction Temperature



Typical Electrical Characteristics (cont.)

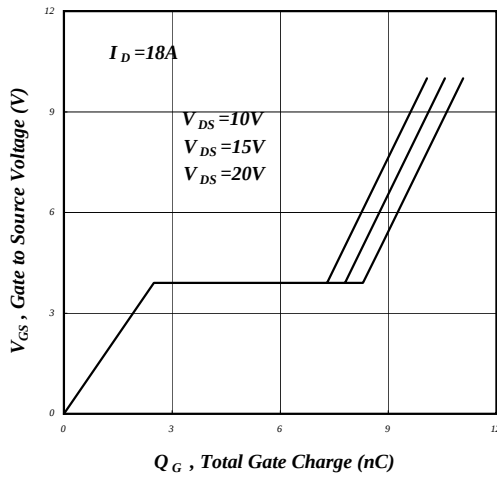


Fig 7. Gate Charge Characteristics

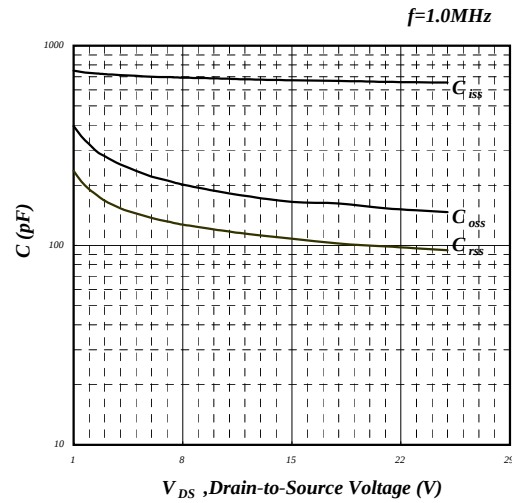


Fig 8. Typical Capacitance Characteristics

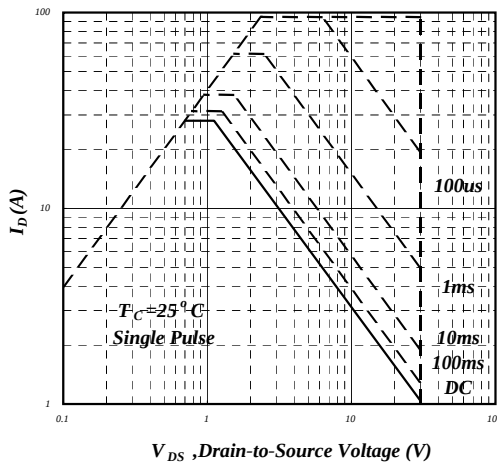


Fig 9. Maximum Safe Operating Area

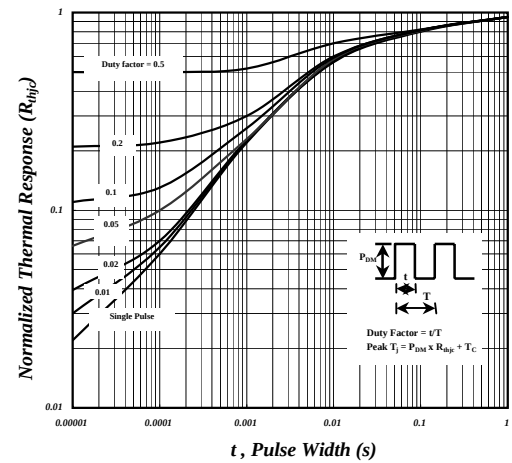


Fig 10. Effective Transient Thermal Impedance

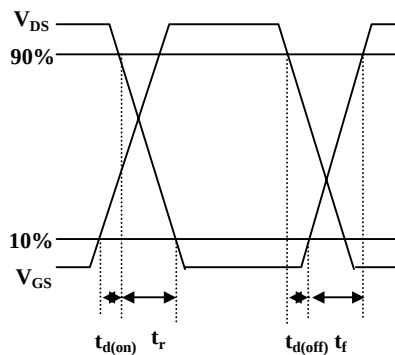


Fig 11. Switching Time Waveforms

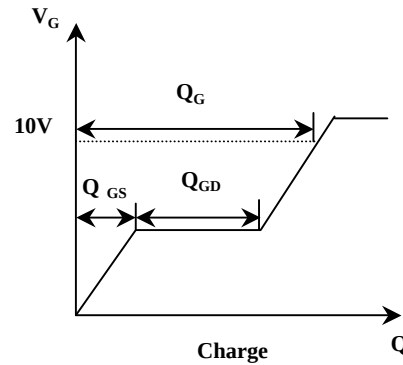
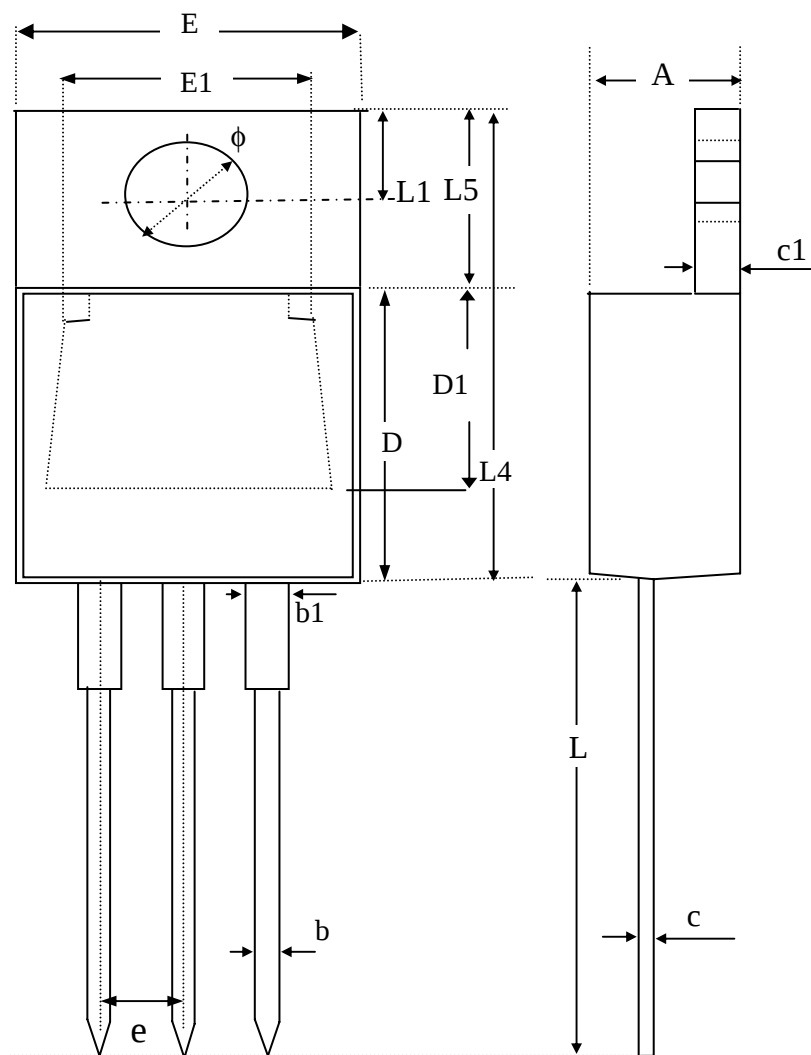


Fig 12. Gate Charge Waveform



Package Dimensions: TO-220

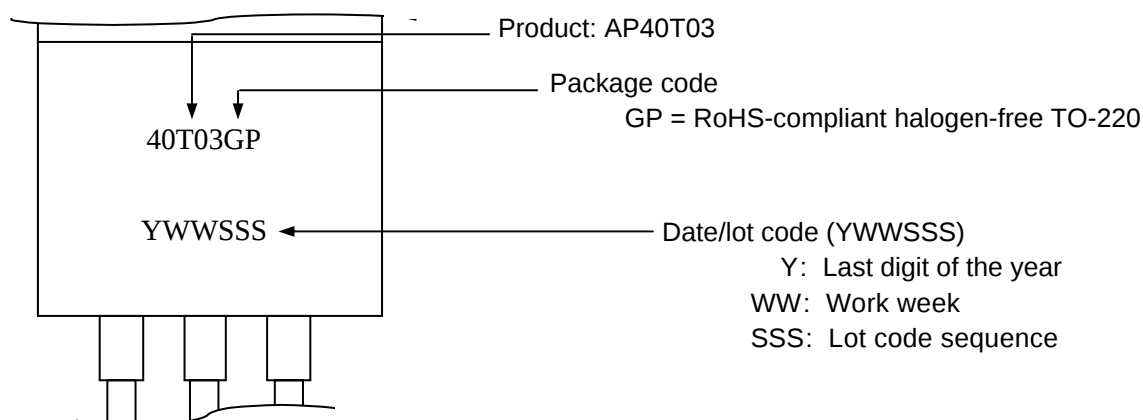


SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.40	4.60	4.80
b	0.76	0.88	1.00
D	8.60	8.80	9.00
c	0.36	0.43	0.50
E	9.80	10.10	10.40
L4	14.70	15.00	15.30
L5	6.20	6.40	6.60
D1	5.10 REF.		
c1	1.25	1.35	1.45
b1	1.17	1.32	1.47
L	13.25	13.75	14.25
e	2.54 REF.		
L1	2.60	2.75	2.89
ϕ	3.71	3.84	3.96
E1	7.4 REF.		

1.All Dimensions Are in Millimeters.

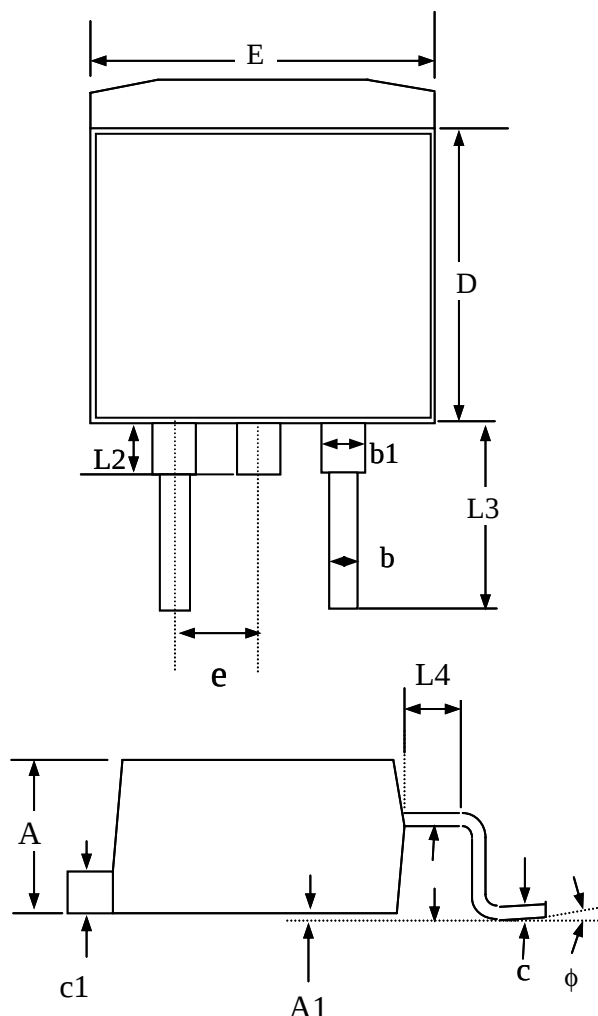
2.Dimension Does Not Include Mold Protrusions.

Marking Information: TO-220





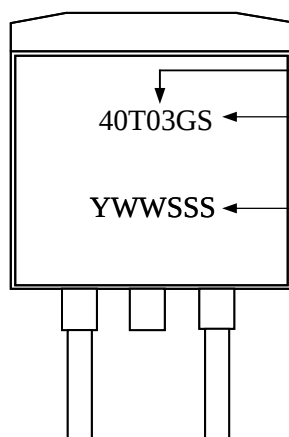
Package Dimensions: TO-263



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.25	4.75	5.20
A1	0.00	0.15	0.30
A2	2.20	2.45	2.70
b	0.70	0.90	1.10
b1	1.07	1.27	1.47
c	0.30	0.45	0.60
c1	1.15	1.30	1.45
D	8.30	8.90	9.40
E	9.70	10.10	10.50
e	2.04	2.54	3.04
L2	-----	1.50	-----
L3	4.50	4.90	5.30
L4	-----	1.50	----

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information: TO-263



Product: AP40T03

Package code:

GS = RoHS-compliant halogen-free TO-263

Date Code (YWWSSS)

Y : Last digit of the year

WW : Work week

SSS : Lot code sequence

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